

**isc Silicon NPN Darlington Power Transistor**
**2SD1829**
**DESCRIPTION**

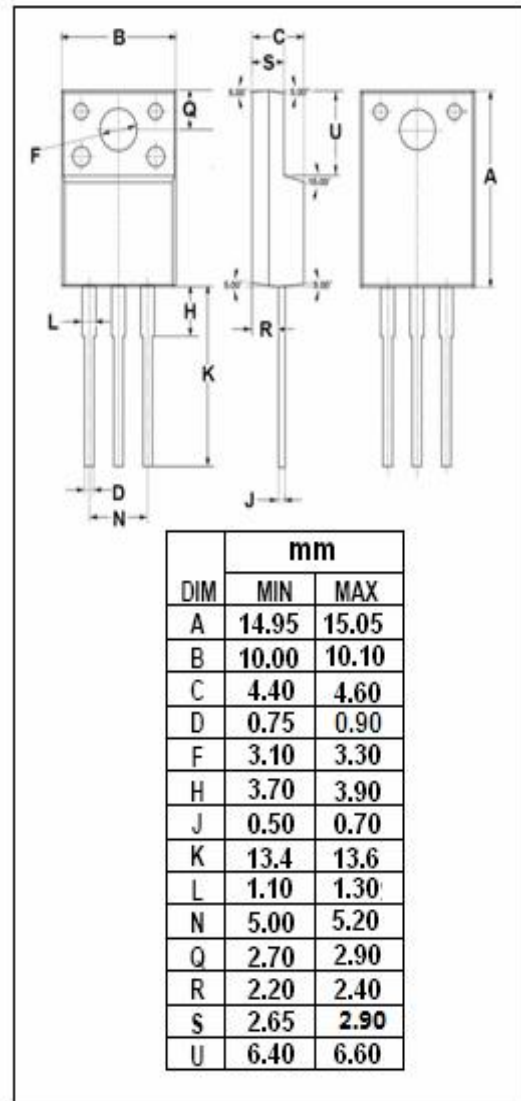
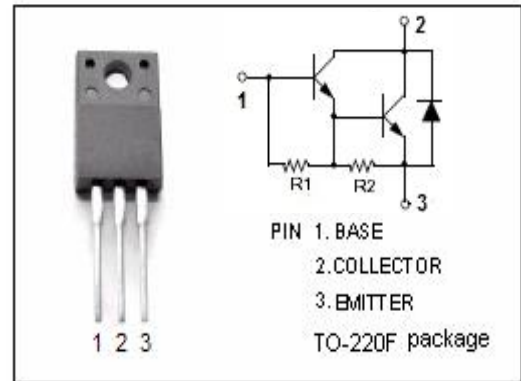
- High DC Current Gain-  
:  $h_{FE} = 1500(\text{Min}) @ (V_{CE} = 3V, I_C = 2.5A)$
- Large Current Capability and Wide ASO.
- Complement to Type 2SB1227
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Designed for use in control of motor drivers, printer hammer drivers, relay drivers, and constant-voltage regulators.

**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	110	V
$V_{CEO}$	Collector-Emitter Voltage	100	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current-Continuous	5	A
$I_{CM}$	Collector Current-Peak	8	A
$P_C$	Collector Power Dissipation @ $T_a = 25^\circ\text{C}$	2	W
	Collector Power Dissipation @ $T_c = 25^\circ\text{C}$	25	
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55~150	$^\circ\text{C}$



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## ELECTRICAL CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 30mA; R <sub>BE</sub> = ∞	100			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 5mA; I <sub>E</sub> = 0	110			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2.5A; I <sub>B</sub> = 5mA			1.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 2.5A; I <sub>B</sub> = 5mA			2.0	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 80V; I <sub>E</sub> = 0			100	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			3.0	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 2.5A; V <sub>CE</sub> = 3V	1500	4000		
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 2.5A; V <sub>CE</sub> = 5V		20		MHz

## Switching Times

t <sub>on</sub>	Turn-on Time			0.6		μ s
t <sub>stg</sub>	Storage Time	I <sub>C</sub> = 2A, I <sub>B1</sub> = -I <sub>B2</sub> = 4mA, V <sub>CC</sub> = 50V; R <sub>L</sub> = 25 Ω		4.8		μ s
t <sub>f</sub>	Fall Time			1.6		μ s

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